

# NPN SILICON RF MICROWAVE TRANSISTOR

**DESCRIPTION:**

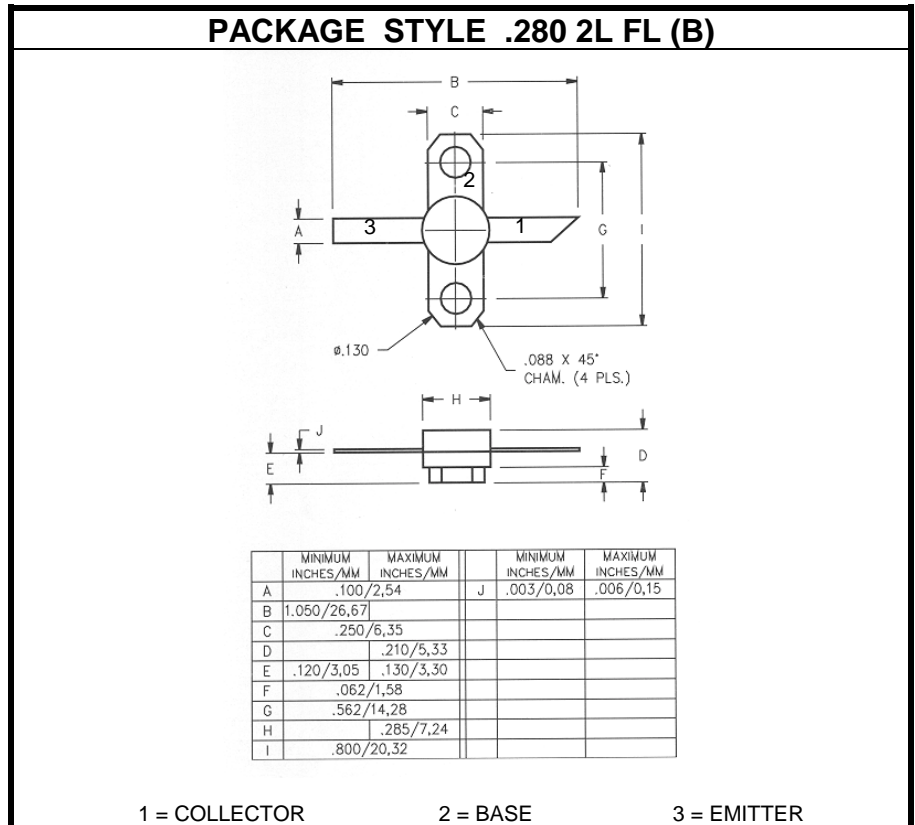
The **ASI MSC80917** is low level Class-C, Common Base Device Designed for IFF, DME driver Applications.

**FEATURES INCLUDE:**

- **Omnigold™** Metalization System
- $P_{OUT}$  4.0 W Min.
- $G_p = 10$  dB

**MAXIMUM RATINGS**

$I_C$	1.0 A
$V_{CE}$	37 V
$P_{DISS}$	7.5 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	35 °C/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 1.0$ mA	45			V
$BV_{CEO}$	$I_C = 5.0$ mA	20			V
$BV_{EBO}$	$I_E = 1.0$ mA	3.5			V
$I_{CES}$	$V_{CE} = 35$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 100$ mA	20		120	
$G_p$	$V_{CE} = 35$ V $P_{IN} = 400$ mW $f = 1025$ to $1150$ MHz PULSE WIDTH = $10$ $\mu$ S      DUTY CYCLE = 1.0%	10			dB
$P_{OUT}$		4.0			W
$\eta$		35			%